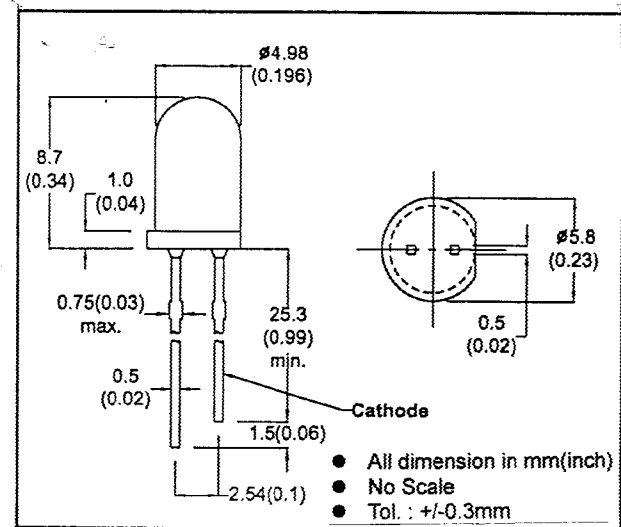


DESCRIPTION

MIB57T-J is a GaAlAs infrared emitting diode molded in clear plastic 5mm diameter package. With the lensing effect of the package, it has an very narrow radiation angle measured from the optical axis to the half power point.



ABSOLUTE MAXIMUM RATINGS

Forward Current (Continuous)	100mA
Pulse Forward Current	1A*
Reverse Voltage (Continuous)	6V
Power Dissipation	175mW
Operating Temperature Range	-20 to +70°C
Lead Soldering Temperature (1/16" from body)	260°C

* Pulse Width = 10 μ s, Duty Ratio = 0.01.

ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	CONDITIONS
Radiant Power Output	Po	2.62	4.5		mW	IF=20mA
Forward Voltage	VF		1.6	2.0	V	IF=100mA
Reverse Current	IR			10	μ A	VR=5V
Peak Wavelength	λ_p		940		nm	IF=20mA
Spectral Line Half Width	$\Delta\lambda$		45		nm	IF=20mA
Viewing Angle	2 θ 1/2		30		degree	IF=20mA



MICRO ELECTRONICS LTD.

38, Hung To Road, Microtron Building, Kwun Tong, Kowloon, Hong Kong.

Kwun Tong P.O. Box 69477 Hong Kong. Fax No. 2341 0321 Telex:43510 Micro Hx. Tel: 2343 0181-5

MIB53T-J

